

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Jonathan J. Wierer, Jr.; Michael R. Krames; Serge L. Rudaz

Assignee: Lumileds Lighting U.S. LLC

Title: Multi-Layer Highly Reflective Ohmic Contacts For Semiconductor

Devices

Serial No.: 09/469,652

Filing Date:

December 22, 1999

Examiner:

Chris C. Chu

Group Art Unit:

2815

Docket No.:

10992873-1 M-9197 US

> San Jose, California February 4, 2003

COMMISSIONER FOR PATENTS Washington, D. C. 20231

**RESPONSE TO OFFICE ACTION** 

Dear Sir:

This responds to the Office Action dated November 4, 2002. Please amend the above-identified application as follows.

## IN THE SPECIFICATION

Please replace the paragraph starting on page 8, line 23 with the following replacement paragraph.

 $\mathcal{D}'$ 

PATENT LAW GROUP LLP 2635 N. FIRST ST. SUITE 223 SAN JOSE, CA 95134 (408) 382-0480 FAX (408) 382-0481 Figure 4 illustrates an alternate embodiment of the multi-layer contact 22 to a semiconductor device 20 with multiple contact layers 22A, 22B, and 22C. Ohmic layer 22A provides ohmic contact to semiconductor 21. A barrier metal layer 22B interposes the ohmic layer 22A and the reflector layer 22C. The barrier layer 22B is used to prevent diffusion of the ohmic layer 22A into the reflector layer 22C, thus preventing the creation of any inter-metallics. These inter-metallics could degrade the specific contact resistance and reflectivity of the contact and thus the efficiency of the device. This is a reliability issue that should be avoided for long lasting devices. The barrier metal layer should be kept thin, e.g. < 100Å, to minimize light absorption and should be as reflective as possible to contribute to the reflectivity of the contact. Exact

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2815

Brian D. Ogonowsky

Carmen C. Cook

David C. Hsia

Rachel V. Leiterman

## February 4, 2003

Box: Non-Fee Amendment Commissioner For Patents Washington, D.C. 20231

Re:

Applicant(s):

Jonathan J. Wierer, Jr.; Michael R. Krames; Serge L. Rudaz

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Transmitted herewith are the following documents in the above-identified application:

Group Art Unit: 2815

M-9197 US

Dear Sir:

<ul> <li>(1) This Transmittal Letter (1 page);</li> <li>(2) Response to Office Action (11 pages).</li> <li>No additional fee is required.</li> <li>The fee has been calculated as shown below:</li> </ul>											CHNOLOGY CENTER	FEB 10 ;	!
		Claims Remainin After Amendmen	<u>t</u>	Highest No. Previously Paid For		Present Extra		<u>Rate</u>		Addit <u>Fee</u>	U.3	2003	[
Total C	Claims	16	Minus	20	=	0	Х	\$18	\$		0.00		
Indeper Claims		2	Minus	3	=	0	х	\$84	\$		0.00		
	Fee of for the first filing of one or more multiple \$ dependent claims per application												
Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.													
Please charge our Deposit Account No. 502226 in the amount of										0.00			
Also, charge any additional fees required and credit any overpayment to our Deposit Account No. 502226.													
							T	otal:	\$		0.00	1	
EXPRESS MAIL LABEL NO:					Respectfully submitted,								
EV 211853950 US					Rachel V. Leiterman								
Attorney for Applicant(s)													

Reg. No. 46,868